2SC5121

Silicon NPN triple diffusion planar type

For general amplification

■ Features

- High collector-base voltage (Emitter open) V_{CBO}
- High collector-emitter voltage (Base open) V_{CEO}
- Small collector output capacitance (Common base, input open circuited) Cob
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings $T_a = 25$ °C

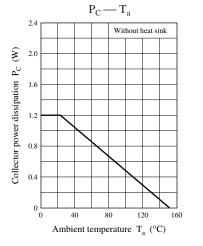
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	400	V	
Collector-emitter voltage (Base open)	V _{CEO}	400	V	
Emitter-base voltage (Collector open)	V_{EBO}	7	V	
Collector current	I_{C}	70	mA	
Peak collector current	I _{CP}	100	mA	
Collector power dissipation	P _C	1.2	W	
Junction temperature	T_{j}	150	°C	
Storage temperature	T _{stg}	−55 to +15 0	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

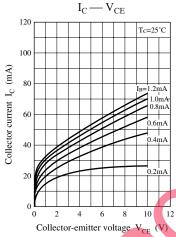
Unit: mm $8.0^{+0.5}_{-0.1}$ 3.2±0.2 ф 3.16±0. 1: Emitter 2: Collector 3: Base TO-126B-A1 Package

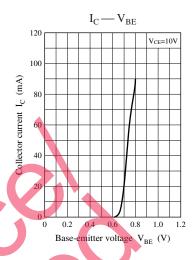
■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

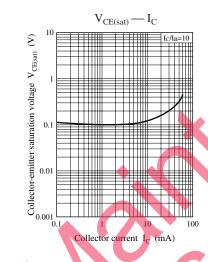
Peak collector current	I_{CP}	100	mA	×	11.				
Collector power dissipation	P _C	1.2	W	10,5°					
Junction temperature T_j 150 °C									
Storage temperature T _{stg} -55 to +150 °C									
Peak collector current Collector power dissipation PC 1.2 W Junction temperature T_j 150 °C Storage temperature T_{stg} -55 to ± 150 °C Electrical Characteristics T_a = 25°C ± 3 °C Collector power dissipation PC 1.2 W Electrical Characteristics T_a = 25°C ± 3 °C Collector power dissipation PC 1.2 W Junction temperature T_stg -55 to ± 150 °C Electrical Characteristics T_a = 25°C ± 3 °C The power dissipation T_a = 25°C ± 3									
Parameter	Symbol		Conditions	Min	Тур	Max	Unit		
Collector-emitter voltage (Base open)	V _{CEO}	$1_{\rm C} = 100$	$\mu A, I_B = 0$	400			V		
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = 1 \mu A$, I _C €03	7			V		
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 30$	0 V, I _E = 0			10	μΑ		
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CH} = 38$	$0 \text{ V. } I_{\text{B}} = 0, T_{\text{a}} = 80^{\circ}\text{C}$			10	μΑ		
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10$	$V_{\bullet}I_{\rm C} = 5 \text{ mA}$	30		100	_		
Collector-emitter saturation voltage *	V _{CE(sat)}	$I_C = 50 \text{ m}$	$A, I_B = 5 \text{ mA}$			1.2	V		
Transition frequency	(Fi	$V_{CB} = 10$	$V, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$	50	80		MHz		
Collector output capacitance (Common base, input open circuited)	Cob	$V_{CB} = 10$	$V, I_E = 0, f = 1 \text{ MHz}$		4	8	pF		

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

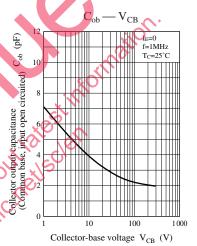












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